

Electronic Supplementary Information to

Branched electron-donor core effect in D- π -A star-shaped small molecules on their properties and performance in single-component and bulk-heterojunction organic solar cells

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1. Experimental part

1.1 Materials

Tetrakis(triphenylphosphine)palladium (0) Pd(PPh₃)₄, malononitrile were obtained from Sigma–Aldrich Co. and used without further purification. THF, toluene, hexane, pyridine were dried and purified according to the known techniques and then used as solvents. *Tris*(4-bromo-2-methoxyphenyl)amine (**1a**) was obtained as described in Ref. [1]. 2,6,10-tribromo-4,4,8,8,12,12-hexakis(4-methylphenyl)-4*H*,8*H*,12*H*-benzo [1,9]quinolizino[3,4,5,6,7-*defg*]acridine (**1b**) was obtained as described in Ref. [2]. 2-hexyl-5,5-dimethyl-2-[5'-(4,4,5,5-tetramethyl-1,3,2-dioxaborolan-2-yl)-2,2'-bithien-5-yl]-1,3-dioxane (**2**) was obtained as described in Ref. [3]. All reactions, unless stated otherwise, were carried out under an inert atmosphere.

1.2 Characterization

¹H NMR spectra were recorded at a “Bruker WP-250 SY” spectrometer, working at a frequency of 250.13 MHz and utilizing CDCl₃ signal (7.25 ppm) as the internal standard. ¹³C NMR spectra were recorded using a “Bruker Avance II 300” spectrometer at 75 MHz. In the case of ¹H NMR spectroscopy, the compounds to be analyzed were taken in the form of 1% solutions in CDCl₃. In the case of ¹³C NMR spectroscopy, the compounds to be analyzed were taken in the form of 5% solutions in CDCl₃. The spectra were then processed using the ACD Labs software.

Elemental analysis of C, N and H elements was carried out using a CHN automatic analyzer (CE 1106). The settling titration using BaCl₂ was applied to analyze Sulfur. The experimental error for elemental analysis is 0.30-0.50%. Knövenagel condensation was carried out in the microwave (Discovery, CEM corporation), using a standard method with the open vessel option, 50 watts. In the case of column chromatography, silica gel 60 (Merck) was taken. Absorption profiles were recorded with an absorption spectrometer (Shimadzu UV 2501 PC). Optical absorption were recorded at room temperature in diluted THF solutions (10⁻⁵ M) and films cast from THF solutions with concentration 10 g/L on quartz substrates.

Cyclic voltammetry measurements were carried out using solid compact layers of the oligomers, which in turn were made by electrostatically rubbing the materials onto a glassy carbon electrode using IPC-Pro M potentiostat. Measurements were made in acetonitrile solution using 0.1 M Bu₄NPF₆ as supporting electrolyte. The scan rate was 200 mV s⁻¹. The glassy carbon electrode was used as a work electrode. Potentials were measured relative to a saturated calomel electrode (SCE). The highest occupied molecular orbital (HOMO) and the lowest unoccupied molecular orbital (LUMO) energies were evaluated using the first standard oxidation (ϕ_{ox}) and reduction (ϕ_{red}) potentials obtained from CV experiments as $E(\text{HOMO}) = -e(\phi_{ox} + 4.40)(\text{eV})$ and $E(\text{LUMO}) = -e(\phi_{red} + 4.40)(\text{eV})$, where e is the elementary charge [4,5].

Thermogravimetric analysis was carried out in a dynamic mode within the temperature range of 30–700 °C using a “Mettler Toledo TG50” system equipped with a microbalance (M3). Heating/cooling rate was chosen to be 10 °C/min. Every compound was studied in air and nitrogen flow of 200 mL/min. Differential scanning calorimetry (DSC) scans were obtained with a “Mettler Toledo DSC30” system with 20 °C/min heating/cooling rate in the temperature range of +20–290 °C for all compounds. N₂ flow of 50 mL/min was used.

The solubility of molecules was measured using their saturated solutions in 1,2-dichlorobenzene, which were prepared by stirring of an excess of solid material in the solvent. For this purpose, the compounds were added in small portions to 1 mL of pure solvent. As prepared, the saturated solution was filtered through 0.25-mm PTFE syringe filters, and the solvent was evaporated using a rotary evaporator. Afterwards the residue was dried in vacuum at 130°C until reaching its constant weight, which was used to calculate the solubility value.

1.3 Synthetic procedures.

***tris*{4-[5'-(2-hexyl-5,5-dimethyl-1,3-dioxan-2-yl)-2,2'-bithien-5-yl]-2-methoxyphenyl}amine (3a).** In an inert atmosphere, degassed solutions of *tris*(4-bromo-2-methoxyphenyl)amine (**1a**) (0.65 g, 1.1 mmol) and 2-hexyl-5,5-dimethyl-2-[5'-(4,4,5,5-tetramethyl-1,3,2-dioxaborolan-2-yl)-2,2'-bithien-5-yl]-1,3-dioxane **2** (2.0 g, 4.4 mmol) in toluene/ethanol mixture (50/5 mL) and 2M solution of aq. Na₂CO₃ (6.1 mL) were added to Pd(PPh₃)₄ (142 mg, 0.1 mmol). The reaction mixture was stirred under reflux for 9 h, and then it was cooled to room temperature and poured into 75 mL of water and 50 mL of toluene. The organic phase was separated, washed with water, dried over sodium sulfate and filtered. The solvent was evaporated in vacuum and the residue was dried at 1 Torr. The product was purified by column chromatography on silica gel (eluent toluene : hexane, 1 : 1) to give pure compound **3a** (1.37 g, 85%) as yellow solid. ¹H NMR (250 MHz, Acetone-d₆): δ [ppm] 0.63 (s, 9H), 0.84 (t, 9H, *J* = 6.7 Hz), 1.18 (s, 9H), 1.20-1.27 (overlapping peaks, 18H), 1.38-1.48 (overlapping peaks, 6H), 1.77-1.86 (overlapping peaks, 6H), 3.41 (d, 6H, *J* = 11.0 Hz), 3.66 (s, 9H), 3.69 (d, 6H, *J* = 11.3 Hz), 6.85 (d, 3H, *J* = 8.2 Hz), 6.88 (d, 3H, *J* = 3.7 Hz), 7.11-7.16 (overlapping peaks, 6H), 7.19 (d, 3H, *J* = 3.7 Hz), 7.25 (d, 3H, *J* = 1.9 Hz), 7.32 (d, 3H, *J* = 3.8 Hz). ¹³C NMR (125 MHz, Acetone-d₆): δ [ppm] 13.43, 21.11, 22.09, 22.34, 22.95, 29.10, 31.65, 44.81, 55.70, 71.39, 99.93, 110.61, 118.25, 123.12, 123.49, 124.57, 125.17, 127.10, 129.83, 135.62, 137.12, 137.37, 143.06, 143.67, 153.72. Calcd (%) for C₈₁H₉₉NO₉S₆: C, 68.37; H, 7.01; S, 13.52; N, 0.98. Found C, 68.48; H, 7.14; S, 13.41; N, 0.95.

2,6,10-*tris*[5'-(2-hexyl-5,5-dimethyl-1,3-dioxan-2-yl)-2,2'-bithien-5-yl]-4,4,8,8,12,12-hexakis(4-methylphenyl)-4*H*,8*H*,12*H*-benzo[1,9]quinolizino[3,4,5,6,7-*defg*]acridine (3b). This compound was obtained according to the procedure described for **3a** using 2,6,10-tribromo-

4,4,8,8,12,12-hexakis(4-methylphenyl)-4*H*,8*H*,12*H*-benzo [1,9]quinolizino[3,4,5,6,7-*defg*]acridine **1b** (1.5 g, 1.4 mmol), 2-hexyl-5,5-dimethyl-2-[5'-(4,4,5,5-tetramethyl-1,3,2-dioxaborolan-2-yl)-2,2'-bithien-5-yl]-1,3-dioxane **2** (2.78 g, 5.7 mmol), Pd(PPh₃)₄ (164 mg, 0.1 mmol), toluene (40 mL), ethanol (4 mL), 2M solution of aq. Na₂CO₃ (8.5 mL). The reaction mixture was stirred under reflux for 9 h, and then it was cooled to room temperature and poured into 50 mL of water and 50 mL of toluene. The organic phase was separated, washed with water, dried over sodium sulfate and filtered. The solvent was evaporated in vacuum and the residue was dried at 1 Torr. The product was purified by column chromatography on silica gel (eluent toluene : hexane, 1 : 1) to give pure compound **3b** (2.0 g, 74%) as yellow solid. ¹H NMR (250 MHz, Acetone-d₆): δ [ppm] 0.62 (s, 9H), 0.83 (t, 9H, *J*=6.8 Hz), 1.17 (s, 9H), 1.21-1.29 (overlapping peaks, 18H), 1.36-1.46 (overlapping peaks, 6H), 1.76-1.84 (overlapping peaks, 6H), 2.31 (s, 18H), 3.38 (d, 6H, *J*=11.2 Hz), 3.65 (d, 6H, *J*=11.0 Hz), 6.76-6.85 (overlapping peaks, 18H), 6.96-7.03 (overlapping peaks, 15H), 7.03 (d, 3H, *J*=3.7 Hz), 7.19 (s, 6H). ¹³C NMR (125 MHz, Acetone-d₆): δ [ppm] 13.29, 20.07, 21.06, 22.04, 22.24, 22.86, 24.16, 29.32, 31.56, 44.65, 55.37, 71.39, 99.94, 123.10, 123.23, 124.62, 125.06, 126.97, 128.38, 128.44, 129.60, 129.87, 134.29, 135.85, 135.92, 137.04, 142.50, 142.57, 144.00. Calcd (%) for C₁₂₃H₁₂₉NO₆S₆: C, 77.36; H, 6.81; S, 10.07; N, 0.73. Found C, 77.48; H, 6.95; S, 10.14; N, 0.71.

1,1',1''-{nitrilotris[(3-methoxy-4,1-phenylene)-2,2'-bithiene-5',5-diyl]}triheptan-1-one (4a). 1M HCl (1.1 mL) was added to a solution of compound **3a** (0.8 g, 0.6 mmol) in THF (15 mL) and then the reaction mixture was stirred for 4 hours at reflux at boiling temperature. After completion of the reaction the organic phase was separated using diethyl ether, washed with water and filtered off to give pure compound **4a** (0.58 g, 88%) as orange powder. ¹H NMR (250 MHz, CDCl₃): δ [ppm] 0.88 (t, 9H, *J*=6.7 Hz), 1.27-1.41 (overlapping peaks, 18H), 1.68-1.79 (overlapping peaks, 6H), 1.77-1.86 (overlapping peaks, 6H), 2.86 (t, 6H, *J*=7.3 Hz), 3.67 (s, 9H), 6.87 (d, 3H, *J*=8.9 Hz), 7.07-7.12 (overlapping peaks, 6H), 7.17 (d, 3H, *J*=4.0 Hz), 7.20 (d, 3H, *J*=4.0 Hz), 7.27 (d, 3H, *J*=3.7 Hz), 7.60 (d, 3H, *J*=4.0 Hz). Calcd (%) for C₆₆H₆₉NO₆S₆: C, 68.07; H, 5.97; S, 16.52; N, 1.20. Found C, 68.16; H, 6.09; S, 16.59; N, 1.16.

1,1',1''-[[4,4,8,8,12,12-hexakis(4-methylphenyl)-4*H*,8*H*,12*H*-benzo[1,9]quinolizino[3,4,5,6,7-*defg*]acridine-2,6,10-triyl]tris(2,2'-bithiene-5',5-diyl)]triheptan-1-one (4b). This compound was obtained according to the procedure described for **4a** using compound **3b** (1.6 g, 0.1 mmol), 1M HCl (4.1 mL), THF (20 mL). After completion of the reaction the organic phase was separated using diethyl ether, washed with water and filtered off to give pure compound **4b** (1.24 g, 90%) as an orange powder. ¹H NMR (250 MHz, CDCl₃): δ [ppm] 0.89 (t, 9H, *J*=6.6 Hz), 1.28-1.43 (overlapping peaks, 18H), 1.68-1.79 (overlapping peaks, 6H), 2.34 (s, 9H), 2.84 (t, 6H, *J*=7.5 Hz),

6.71 (d, 12H, $J=8.1$ Hz), 6.80 (d, 3H, $J=3.8$ Hz), 6.91 (d, 12H, $J=8.2$ Hz), 7.07 (d, 3H, $J=4.0$ Hz), 7.12 (s, 6H), 7.14 (d, 3H, $J=3.8$ Hz), 7.55 (d, 3H, $J=4.1$ Hz). ^{13}C NMR (125 MHz, CDCl_3): δ [ppm] 14.02, 20.97, 22.48, 24.90, 28.99, 31.58, 38.97, 55.27, 123.23, 123.67, 125.16, 126.42, 128.08, 128.37, 129.49, 129.92, 132.51, 134.52, 134.70, 135.70, 142.00, 142.20, 145.30, 145.35, 193.14. Calcd (%) for $\text{C}_{108}\text{H}_{99}\text{NO}_3\text{S}_6$: C, 78.55; H, 6.04; S, 11.65; N, 0.85. Found C, 78.71; H, 6.26; S, 11.52; N, 0.83.

***tris*{4-[5'-(1,1-dicyanooct-1-en-2-yl)-2,2'-bithien-5-yl]-2-methoxyphenyl}amine (m-TPA).**

Compound **4a** (0.53 g, 0.5 mmol), malononitrile (0.45 g, 6.8 mmol) and dry pyridine (12.0 mL) were placed in a reaction vessel and stirred under argon atmosphere for 11 hours at reflux using the microwave heating. After completeness of the reaction, pyridine was evaporated in vacuum and the residue was dried at 1 Torr. The crude product was purified by column chromatography on silica gel (eluent methylene chloride). Further purification included precipitation of the product from its THF solution with toluene and hexane to give pure product as a black solid (0.3 g, 51%). ^1H NMR (250 MHz, CDCl_3): δ [ppm] 0.93 (t, 9H, $J=7.0$ Hz), 1.32-1.41 (overlapping peaks, 12H), 1.45-1.55 (overlapping peaks, 6H), 1.68-1.79 (overlapping peaks, 6H), 2.94 (t, 6H, $J=7.6$ Hz), 3.70 (s, 9H), 6.93 (d, 3H, $J=8.8$ Hz), 7.13-7.18 (overlapping peaks, 6H), 7.25 (d, 3H, $J=4.0$ Hz), 7.28 (d, 3H, $J=4.3$ Hz), 7.35 (d, 3H, $J=4.0$ Hz), 7.95 (d, 3H, $J=4.3$ Hz). ^{13}C NMR (125 MHz, CDCl_3): δ [ppm] 13.82, 22.35, 29.13, 30.36, 31.23, 37.49, 56.20, 76.76, 110.78, 113.77, 114.59, 118.79, 123.74, 124.67, 125.18, 127.51, 129.61, 133.66, 135.00, 135.20, 137.51, 146.77, 147.00, 153.58, 166.23. Calcd (%) for $\text{C}_{75}\text{H}_{69}\text{N}_7\text{O}_3\text{S}_6$: C, 68.83; H, 5.31; S, 14.70; N, 7.49. Found C, 68.96; H, 5.42; S, 14.77; N, 7.43.

2,2',2''-[[4,4,8,8,12,12-hexakis(4-methylphenyl)-4H,8H,12H-benzo[1,9]quinolizino[3,4,5,6,7-defg]acridine-2,6,10-triyl]tris(2,2'-bithiene-5',5-diylhept-1-yl-1-ylidene)]trimalononitrile (f-TPA).

This compound was obtained according to the procedure described for **m-TPA** using compound **4b** (1.1 g, 0.7 mmol), malonitrile (0.31 g, 4.7 mmol), and pyridine (17 mL). The crude product was purified by column chromatography on silica gel (eluent methylene chloride). Further purification included precipitation of the product from its THF solution with toluene and hexane to give pure product as a black solid (0.84 g, 70%). ^1H NMR (250 MHz, CDCl_3): δ [ppm] 0.92 (t, 9H, $J=7.1$ Hz), 1.31-1.39 (overlapping peaks, 12H), 1.43-1.54 (overlapping peaks, 6H), 2.35 (s, 18H), 2.92 (t, 6H, $J=7.8$ Hz), 6.74 (d, 12H, $J=8.2$ Hz), 6.84 (d, 3H, $J=3.8$ Hz), 6.94 (d, 12H, $J=8.2$ Hz), 7.16 (s, 6H), 7.18 (d, 3H, $J=4.3$ Hz), 7.20 (d, 3H, $J=3.8$ Hz), 7.92 (d, 3H, $J=4.3$ Hz). ^{13}C NMR (125 MHz, CDCl_3): δ [ppm] 13.82, 20.87, 22.34, 29.11, 30.32, 31.23, 37.54, 55.44, 76.78, 113.77, 114.57, 123.59, 124.78, 125.48, 127.50, 127.99, 128.46, 129.73, 129.99, 133.62, 134.75, 134.87,

135.20, 135.90, 142.31, 146.73, 146.84, 166.23. Calcd (%) for $C_{117}H_{117}NS_6$: C, 81.25; H, 6.82; S, 11.12; N, 0.81. Found C, 81.35; H, 6.74; S, 11.12; N, 0.78.

2. ^1H and ^{13}C NMR Spectra

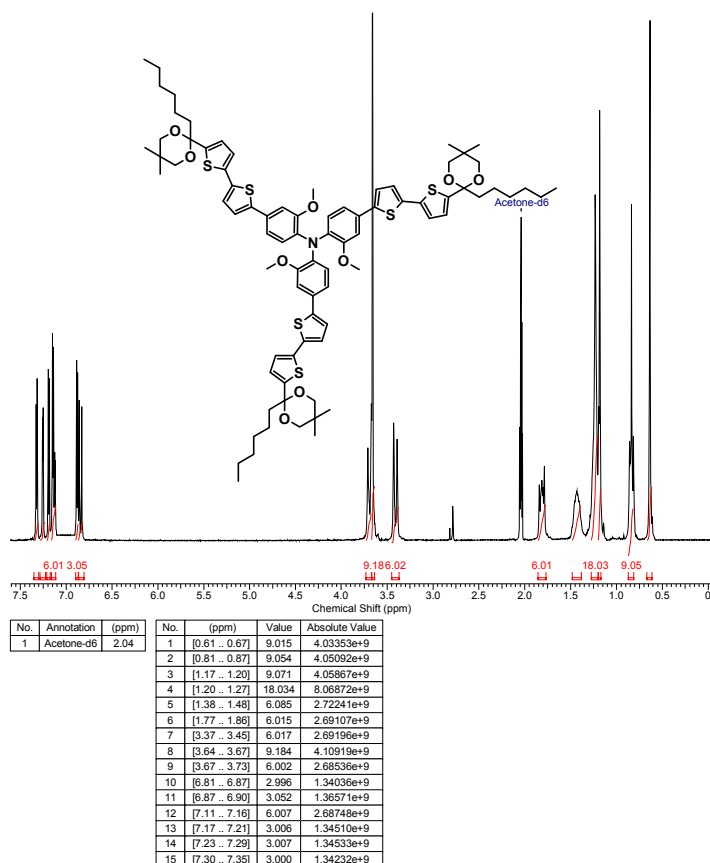


Figure S2.1. ^1H NMR spectrum of compound **3a** in Acetone- d_6 .

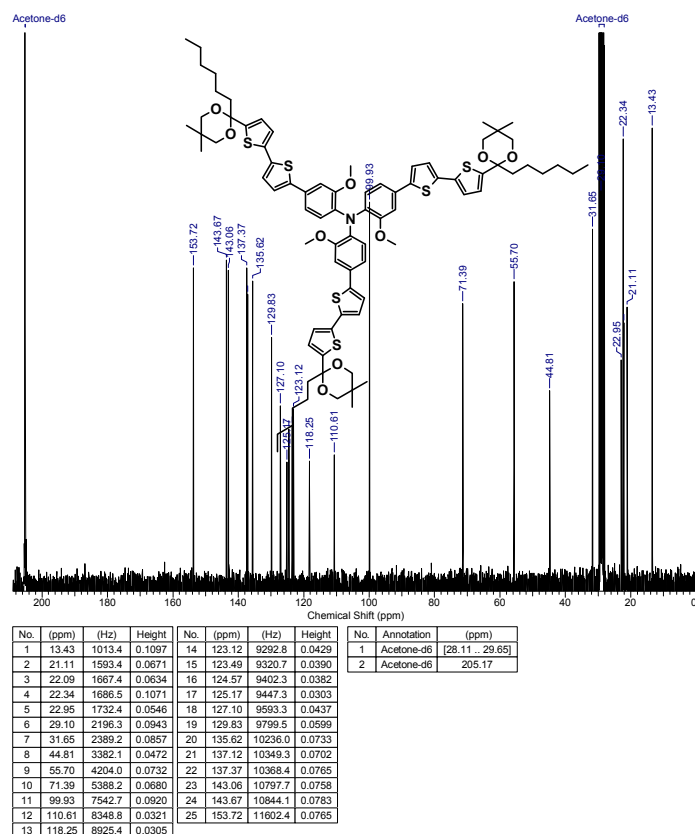


Figure S2.2. ^{13}C NMR spectrum of compound **3a** in Acetone- d_6 .

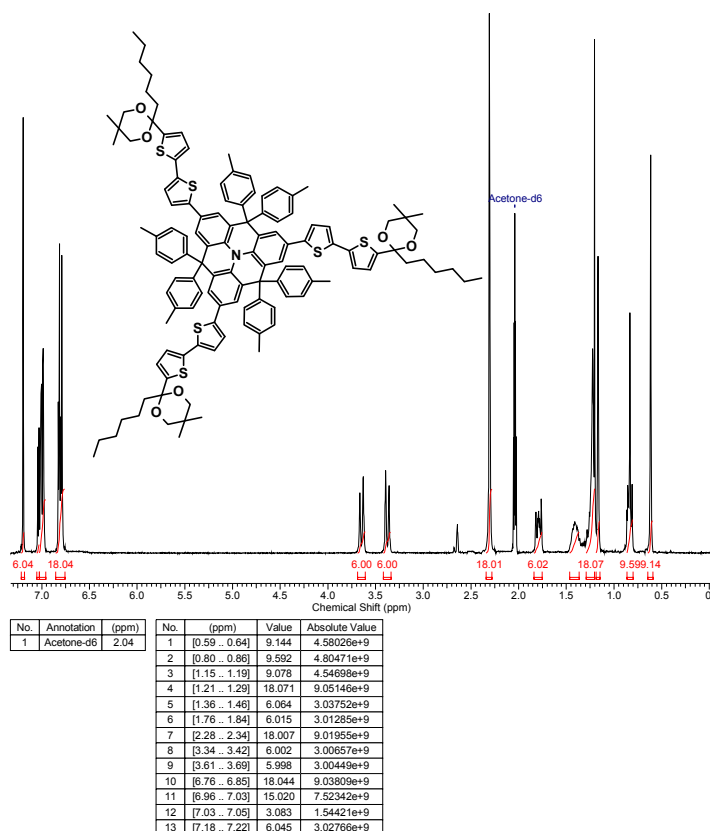
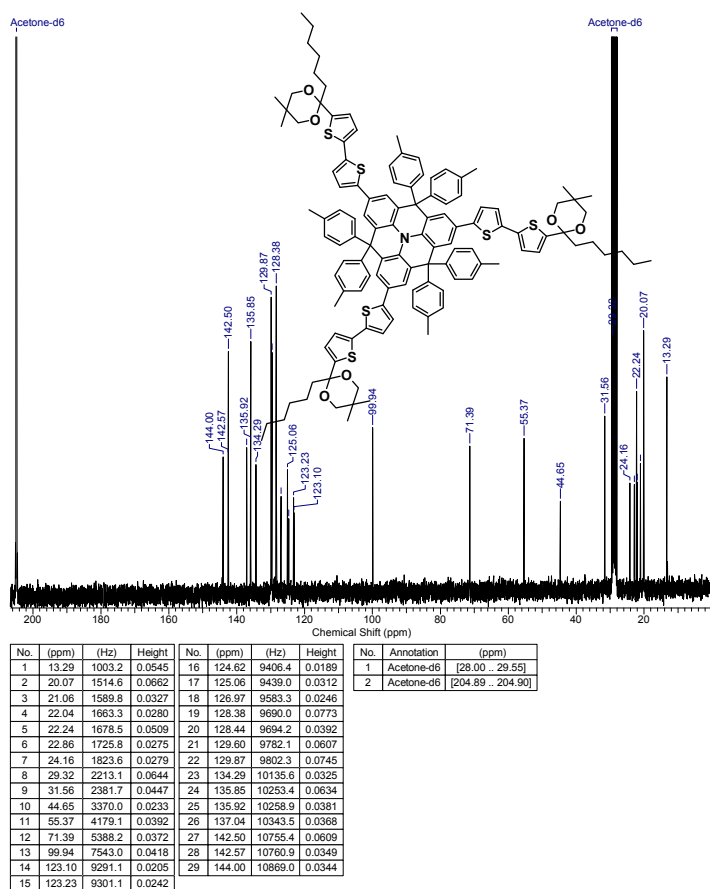


Figure S2.3. ^1H NMR spectrum of compound **3b** in Acetone- d_6 .



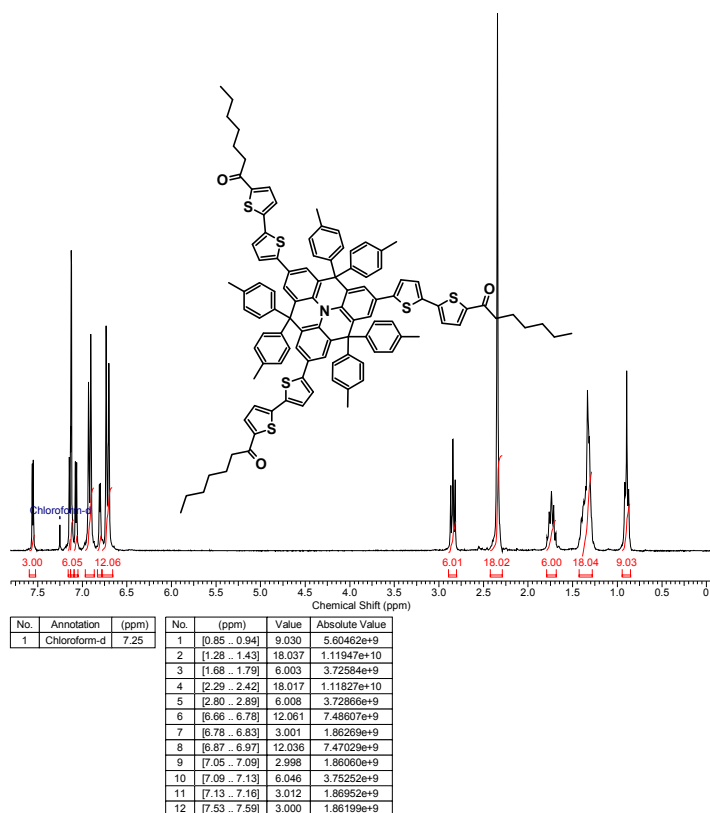


Figure S2.5. ^1H NMR spectrum of compound 4a in CDCl_3 .

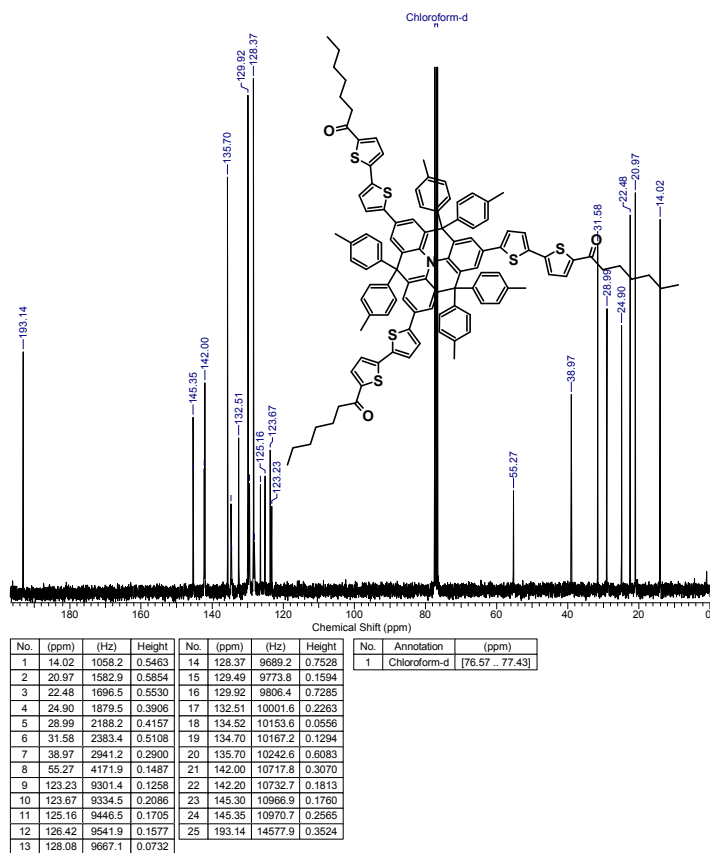


Figure S2.6. ^{13}C NMR spectrum of compound 4a in CDCl_3 .

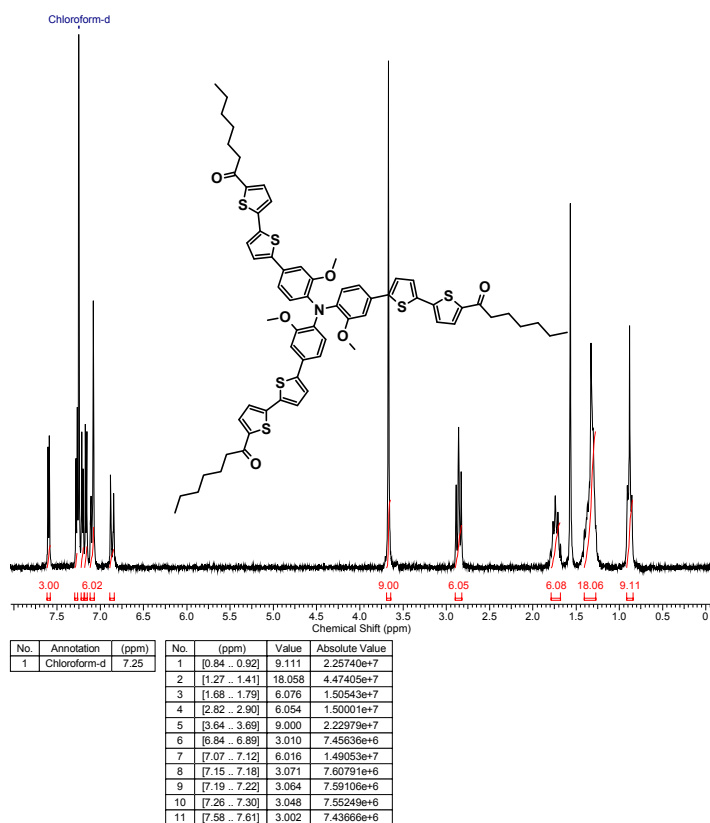


Figure S2.7. ^1H NMR spectrum of compound **4b** in CDCl_3 .

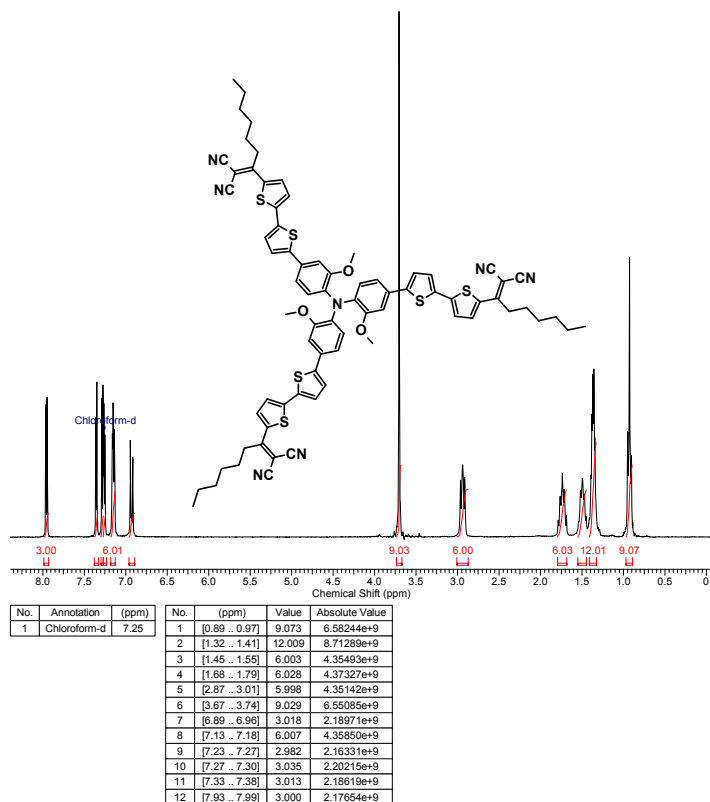


Figure S2.8. ^1H NMR spectrum of compound **m-TPA** in CDCl_3 .

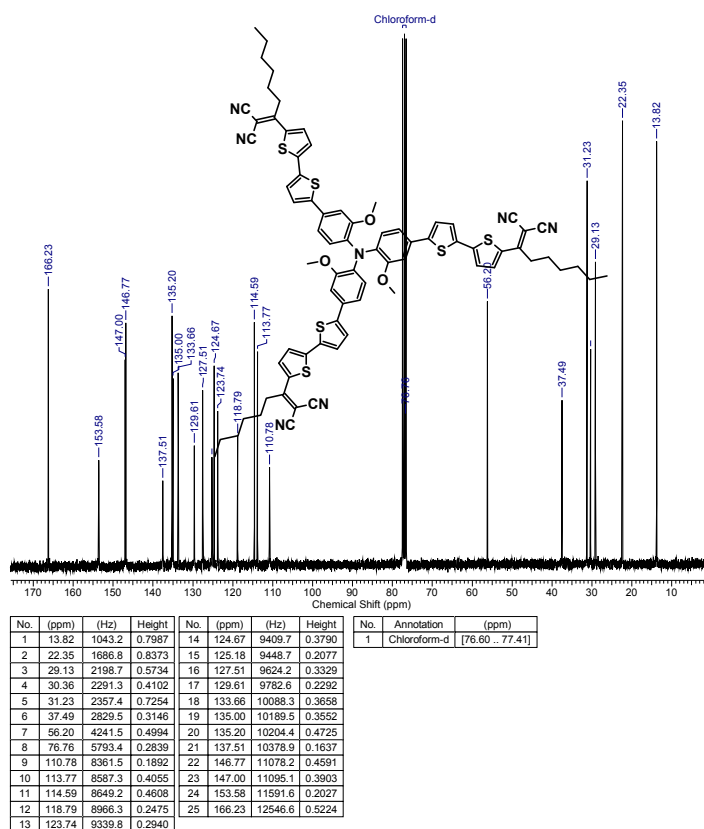


Figure S2.9. ^{13}C NMR spectrum of compound **m-TPA** in CDCl_3 .

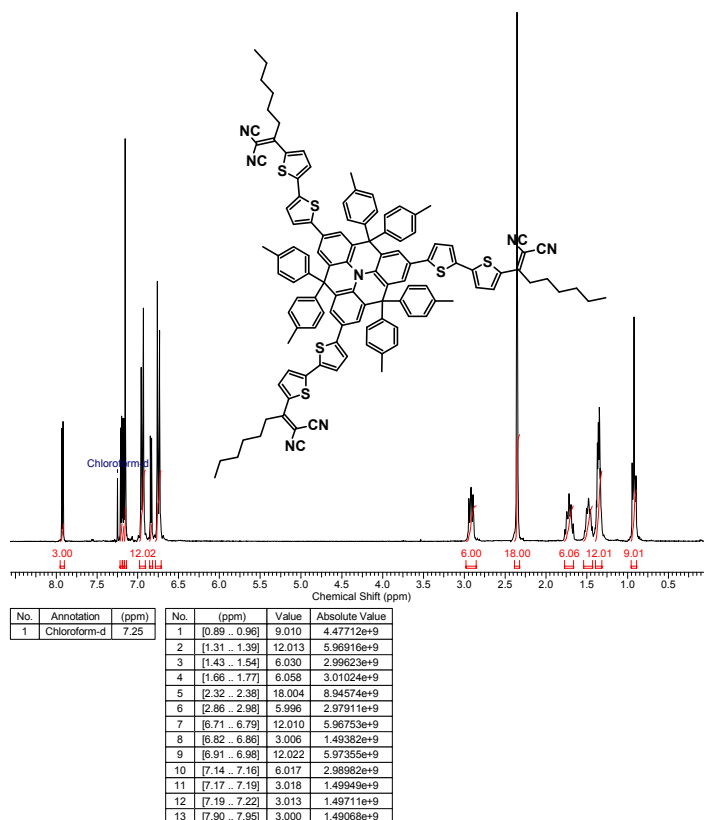


Figure S2.10. ^1H NMR spectrum of compound **f-TPA** in CDCl_3 .

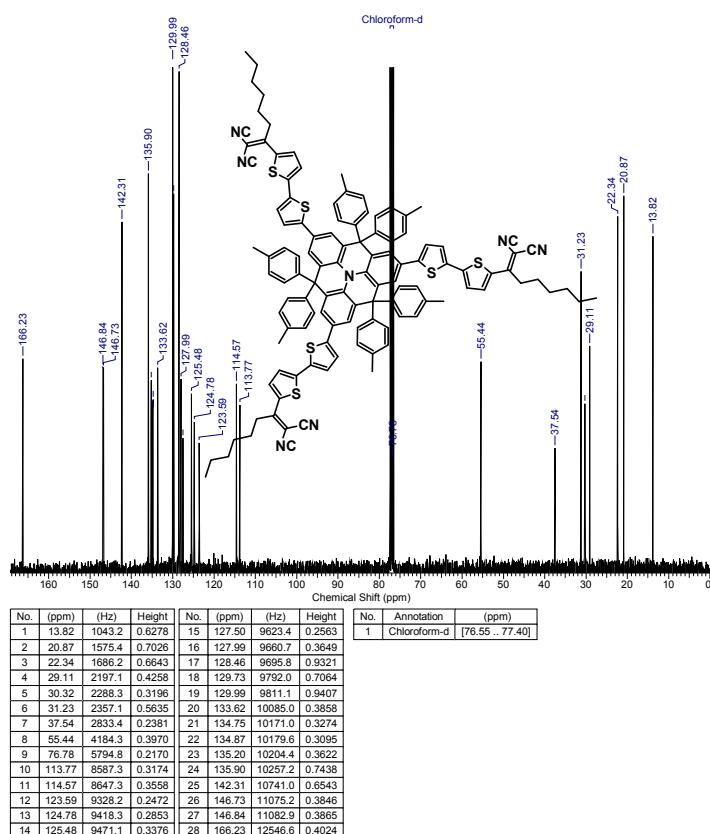


Figure S2.11. ^{13}C NMR spectrum of compound **f-TPA** in CDCl_3 .

3. Charge transport and photovoltaic properties

3.1. Solar cells fabrication and characterization

The samples of organic solar cells were prepared in the following way. First, glass substrates coated with patterned indium-tin oxide (ITO) layer (Xin Yan Technology Limited) were cleaned in an ultrasonic bath with a surfactant and isopropanol and then exposed to an ultraviolet lamp (Photo Surface Processor PL16-110, Sen Lights Corporation, 15 mW/cm², 254 nm). Then a 50-nm-thick layer of poly(ethylenedioxythiophene):polystyrene sulfonate (PEDOT:PSS, CLEVIO P VP AI 4083, Heraeus GmbH, Germany) was deposited on the ITO by spin coating at 3000 rpm and annealed at 140 °C for 15 minutes. The active layer was deposited on the PEDOT:PSS layer by doctor blading from chloroform solution with a concentration of 11 g/L, at 50°C (the resulting thickness was 55±5 nm) for single component cells or from orthodichlorobenzene solution with a concentration of 24 g/L, 90°C (the resulting thickness was 85±5 nm) for BHJ cells. On top of the active layer Ca (20 nm) / Al (80 nm) electrode was evaporated under pressure less than 5·10⁻⁶ mbar with the use of a vacuum evaporator (Univex 300, Leybold) integrated in a glove box with Ar atmosphere (H₂O < 0.1 ppm, O₂ < 5 ppm). Eight devices with the active area of each device 3 mm² were formed on substrates by using a shadow mask.

All the electrical measurements were performed in a glove box with Ar atmosphere (H₂O < 0.1 ppm, O₂ < 5 ppm). *J-V* characteristics of cells were measured using a source-meter (SourceMeter 2400, Keithley) in dark and under light of a solar simulator (Newport 67005) with an intensity of 100 mW/cm² (AM1.5G).

External quantum efficiency (EQE) spectra were measured with the use of a laser-driven light source (LDLS EQ-99X, Energetiq) equipped by a monochromator (CS130-USB-3-MC, Newport), a power sensor (S120UV, Thorlabs) and source-meter (SourceMeter 2400, Keithley). To avoid higher diffraction orders, additional filters KG3, GG400, OG550 (Newport) were used for 380-500, 480-620 and 600-800 nm spectral ranges respectively.

To study the surface morphology of the active layer, an atomic force microscope (AFM) (SOLVER NEXT, NT-MDT) operating in the semi-contact mode was used. Probes (HA_FM ETALON, NT-MDT) with the tip radius of curvature of 10 nm, the resonant frequencies of 77 – 114 kHz and force constant of 3.5 – 6 N/m were used.

3.2. Mobility measurements

Charge-carrier mobility were determined from space charge limited current (SCLC) measurements on unipolar thin-film devices of several thicknesses. Unipolar devices were made similarly to solar cells. The structure of the hole-only devices was ITO/PEDOT:PSS/active layer/Ag. The structure of the electron-only devices was ITO/ZnO/active layer/Ca. The ZnO layer was deposited on the ITO layer in the following way. First, 100 mg of zinc acetate dihydrate were dissolved in a mixture of 1 mL of 2-methoxyethanol and 27 µL of monoethanolamine. Then, this solution was bladed on the ITO layer and annealed at 140 °C for 25 minutes, resulting in a 40 nm-ZnO layer. Eight devices were formed on one substrate. The hole and electron mobilities were extracted by fitting the current–voltage (*J-V*) characteristics of the corresponding devices with the simplest SCLC model.

According to the simplest SCLC model and taking into account the series (R_s) and shunt (R_{sh}) resistances (as fitting parameters), the charge mobility was calculated by approximating the dark J - V curves of unipolar devices using the following equation:

$$J = \frac{9}{8} \epsilon \epsilon_0 \mu \frac{(V - V_{BI} - JSR_s)^2}{d^3} + \frac{V - JSR_s}{R_{sh}},$$

where $\epsilon_0 = 8.85 \cdot 10^{-12}$ F/m, ϵ is the dielectric permittivity (taken as 3), d is the active layer thickness (measured by AFM), V_{BI} is the built-in voltage (fitting parameter).

3.3. Hole mobility in pristine films

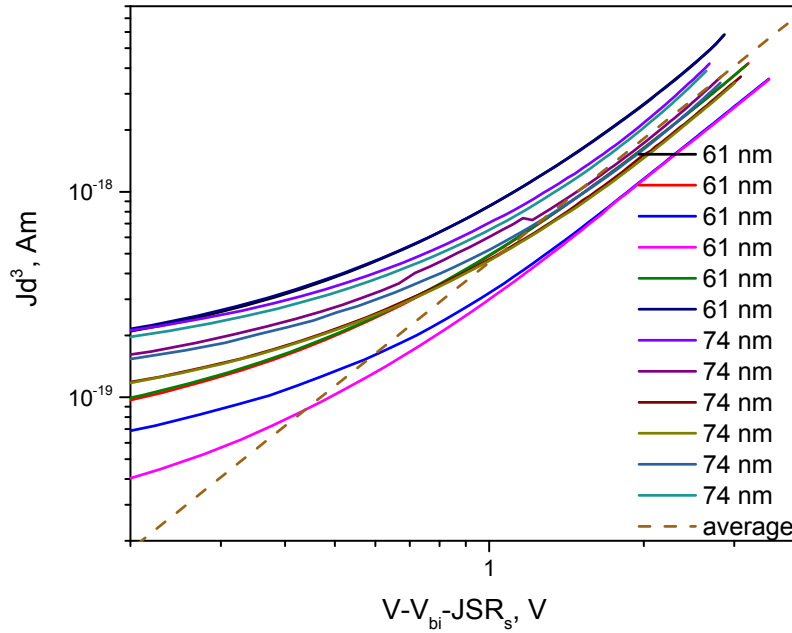


Figure S3.1. J - V characteristics of TPA hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (61 ± 5 and 74 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

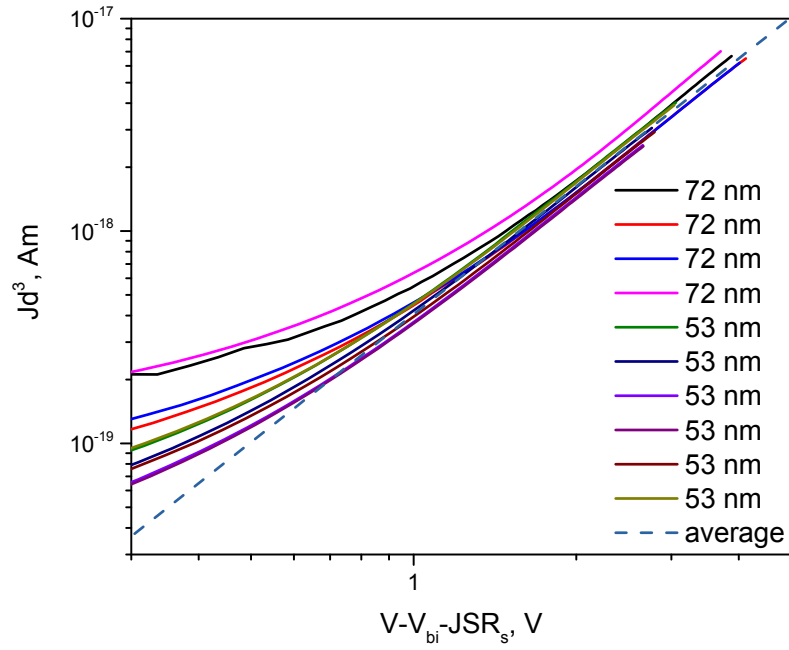


Figure S3.2. J - V characteristics of **m-TPA** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (53 ± 5 and 72 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

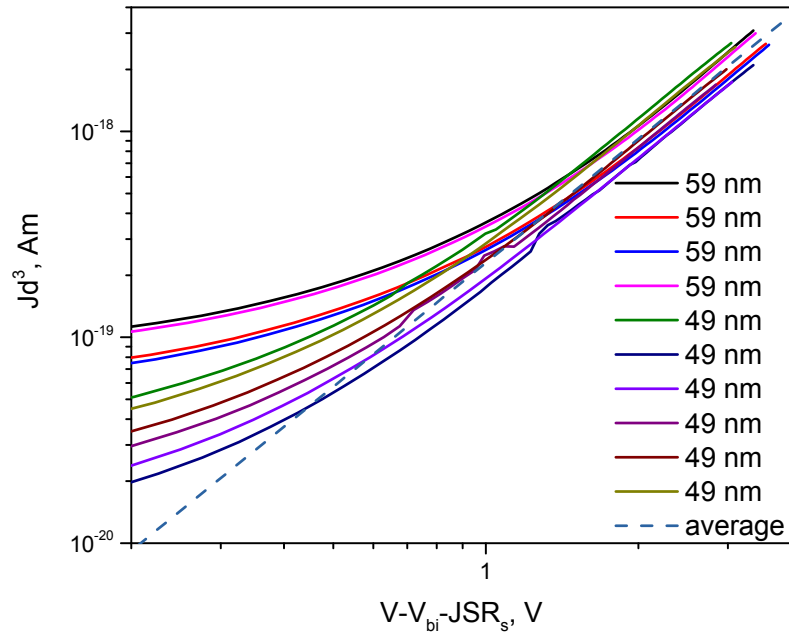


Figure S3.3. J - V characteristics of **f-TPA** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (49 ± 5 and 59 ± 5 nm) against the voltage, corrected for the built-in

voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

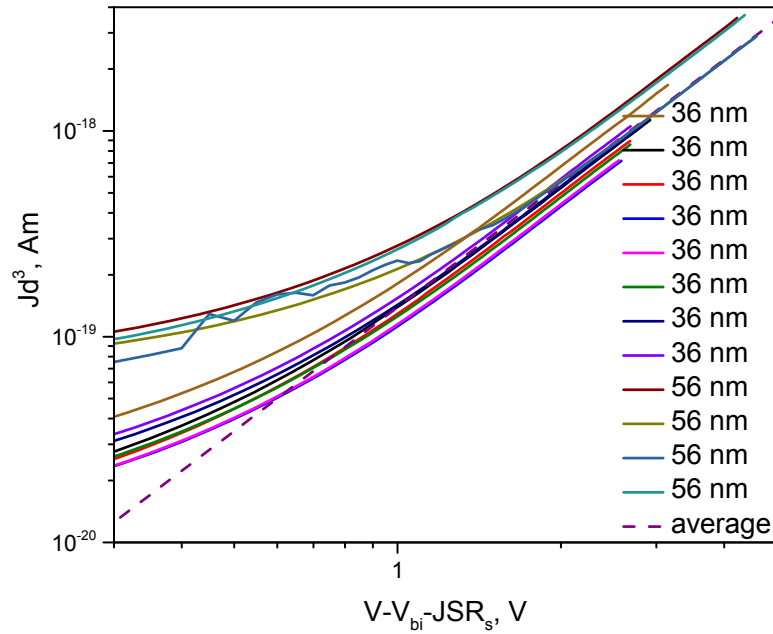


Figure S3.4. J - V characteristics of **s-CBZ** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (36 ± 5 and 56 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

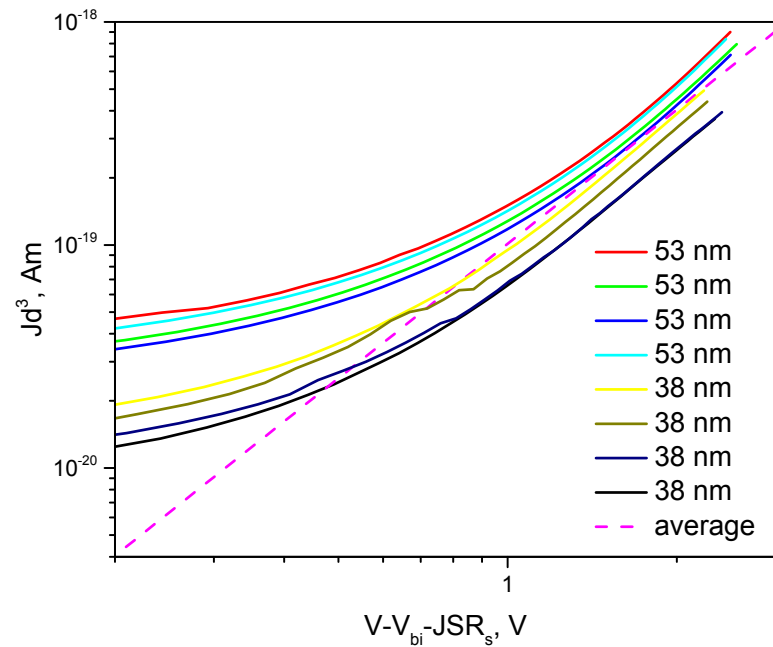


Figure S3.5. J - V characteristics of **t-CBZ** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (38 ± 5 and 53 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

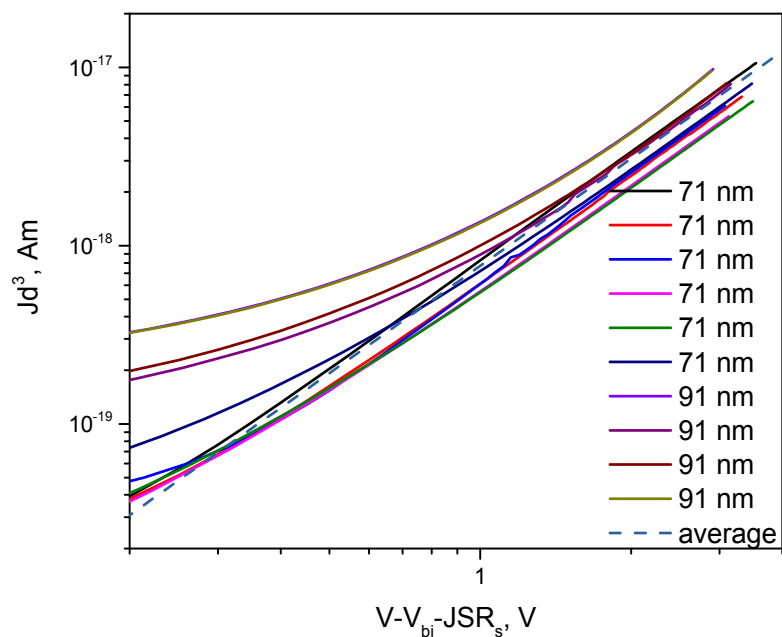


Figure S3.6. J - V characteristics of **BTI** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (71 ± 5 and 91 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

3.4. Electron mobility in pristine films

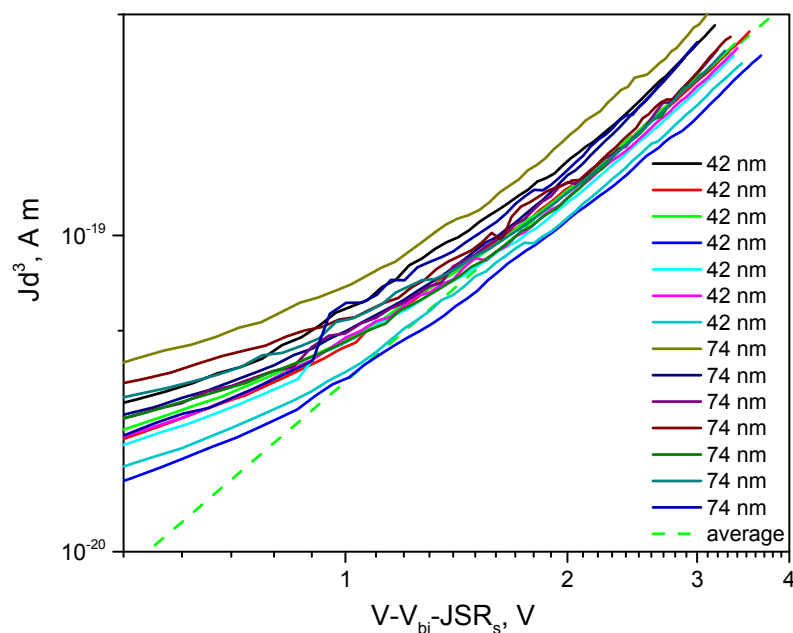


Figure S3.7. J - V characteristics of **TPA** electron only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (42 ± 5 and 74 ± 5 nm) against the voltage, corrected for the built-in

voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the electron mobility is extracted.

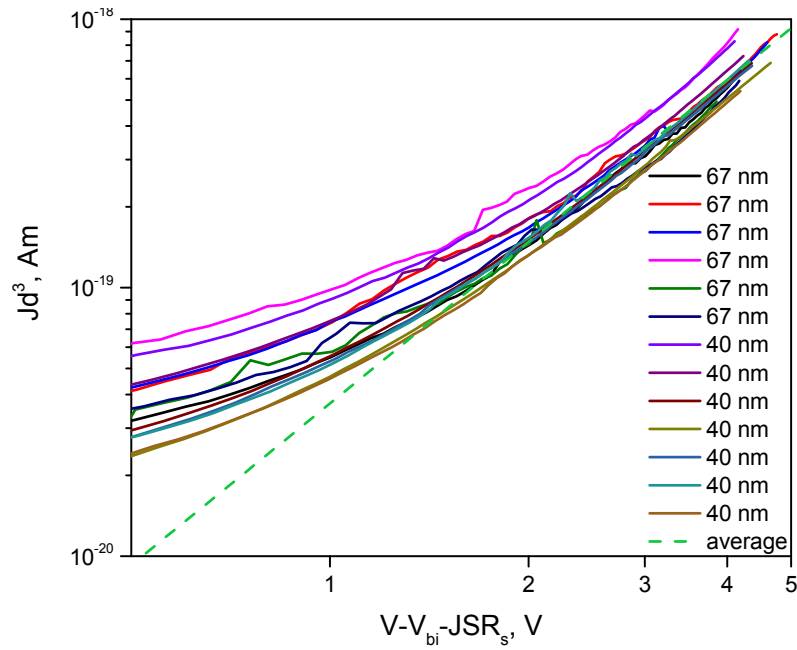


Figure S3.8. J - V characteristics of **m-TPA** electron only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (40 ± 5 and 67 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the electron mobility is extracted.

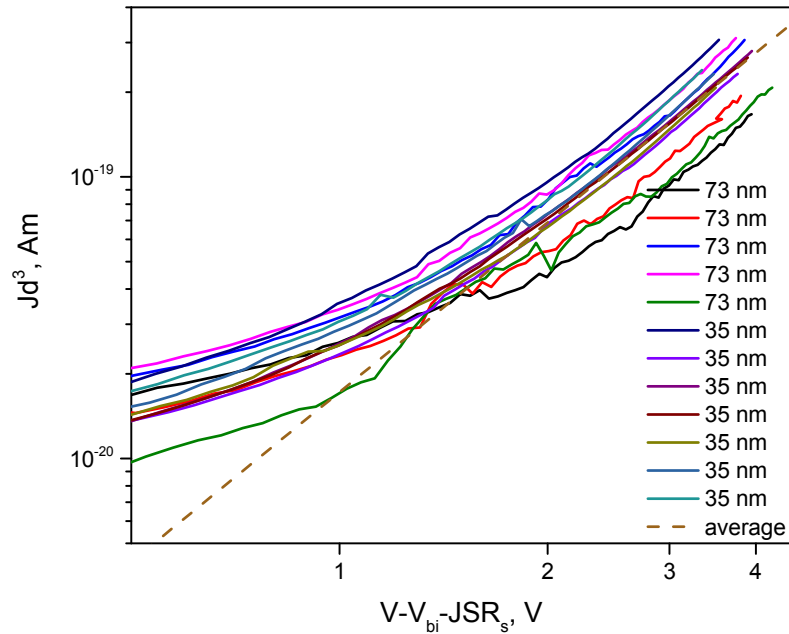


Figure S3.9. J - V characteristics of **f-TPA** electron only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (35 ± 5 and 73 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the electron mobility is extracted.

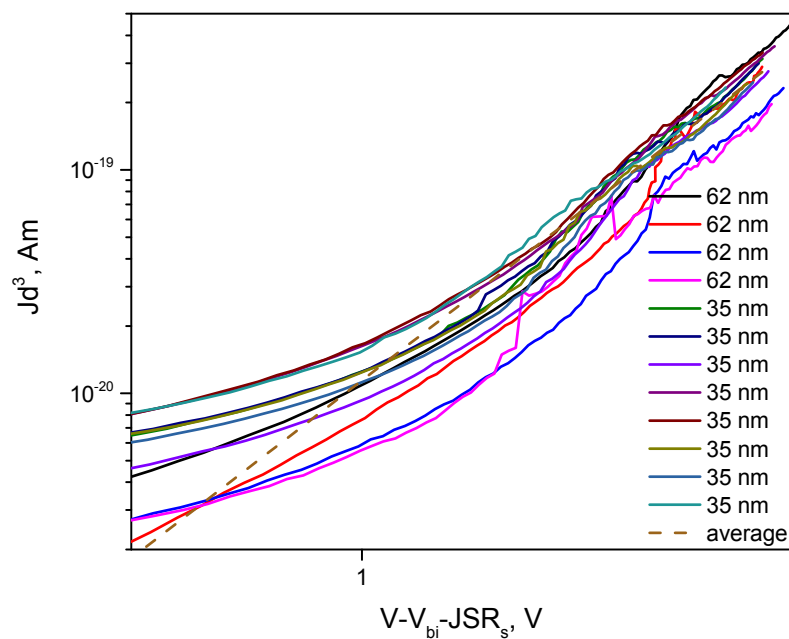


Figure S3.10. J - V characteristics of **s-CBZ** electron only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (35 ± 5 and 62 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the electron mobility is extracted.

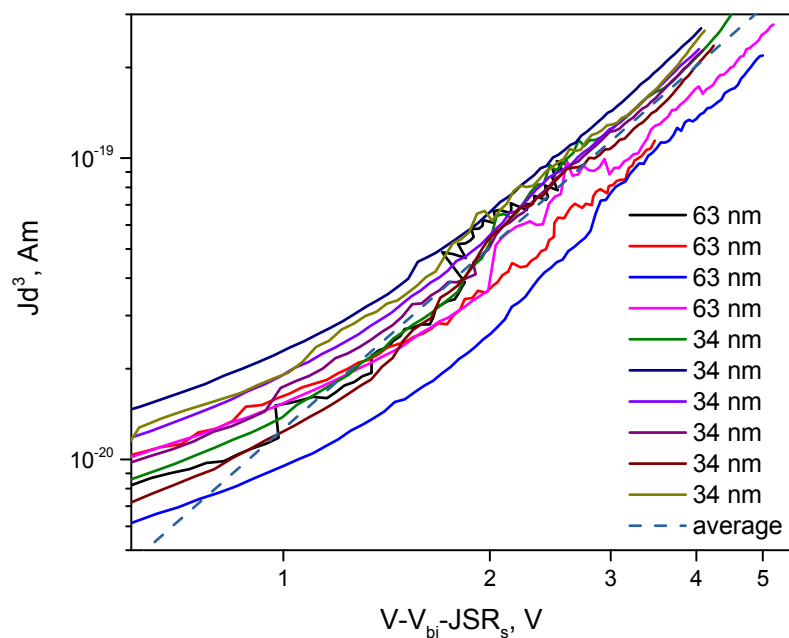


Figure S3.11. J - V characteristics of **t-CBZ** electron only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (34 ± 5 and 63 ± 5 nm) against the voltage, corrected for the built-in

voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the electron mobility is extracted.

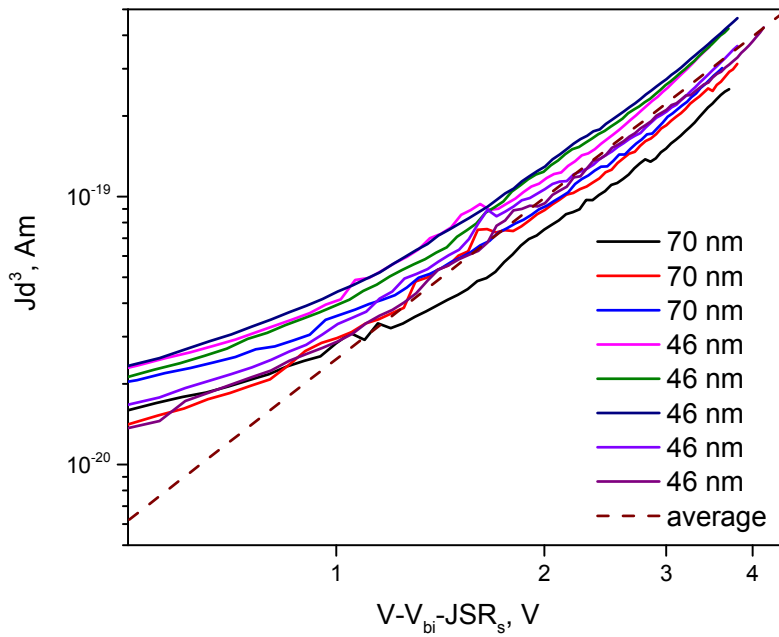


Figure S3.12. J - V characteristics of BTI electron only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (46 ± 5 and 70 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the electron mobility is extracted.

3.5. Hole mobility in blended films

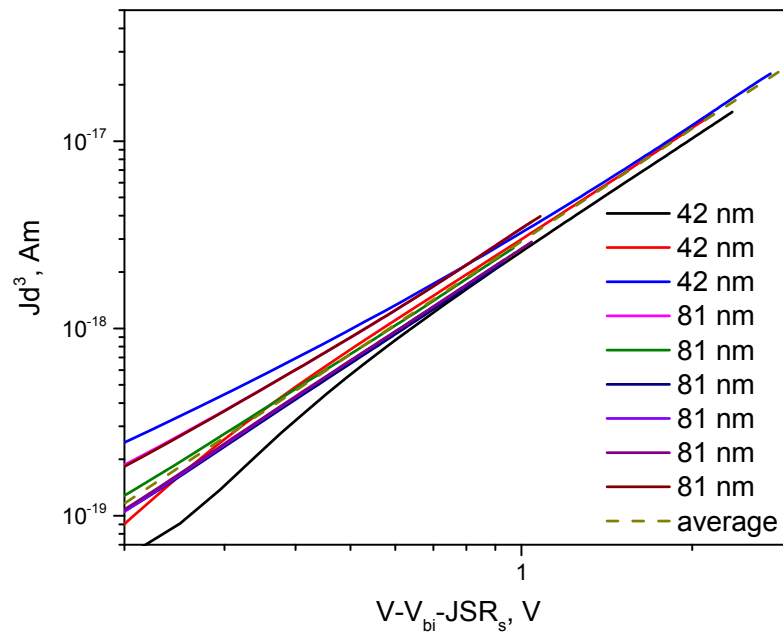


Figure S3.13. J - V characteristics of **TPA:PC₇₁BM** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (42 ± 5 and 81 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

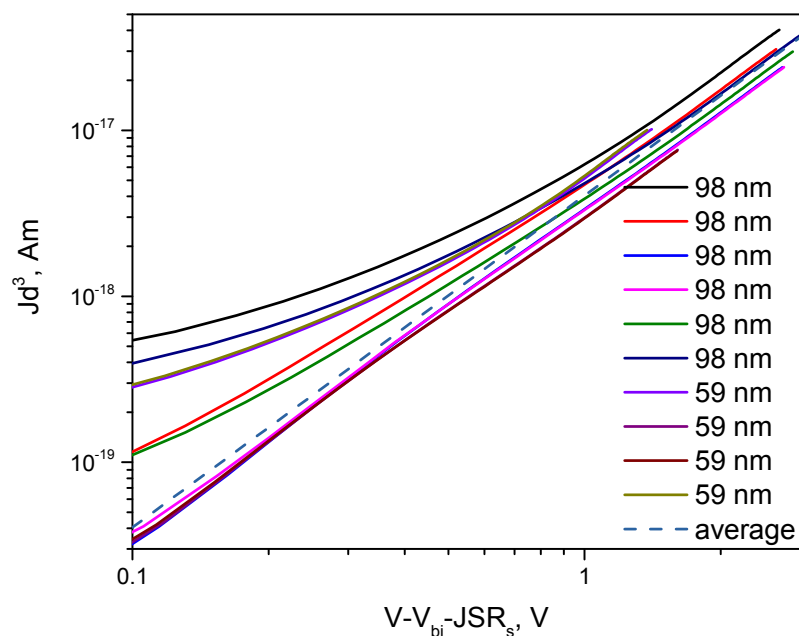


Figure S3.14. J - V characteristics of **m-TPA:PC₇₁BM** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (59 ± 5 and 98 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

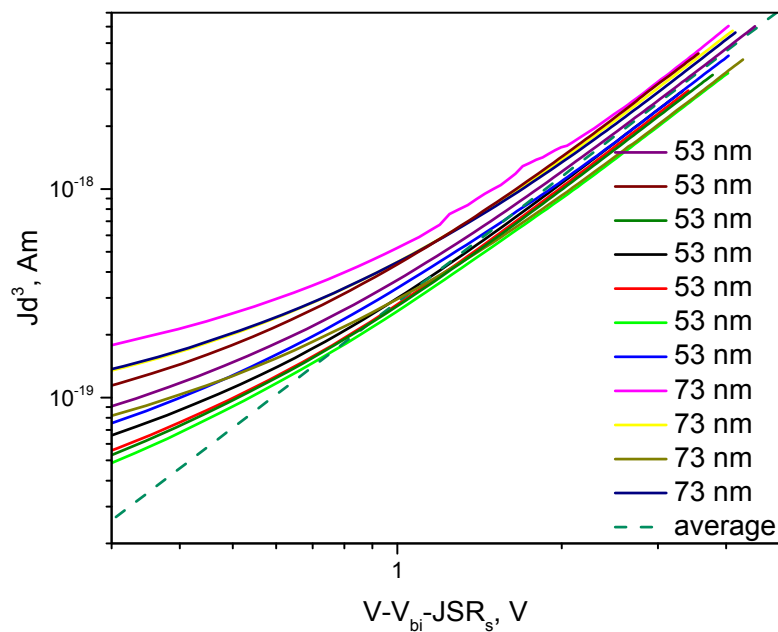


Figure S3.15. J - V characteristics of **f-TPA:PC₇₁BM** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (53 ± 5 and 73 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

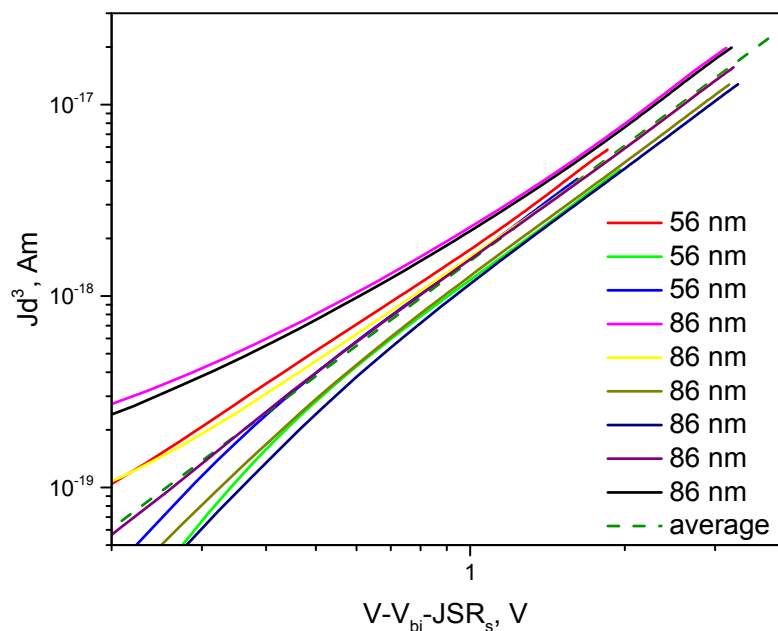


Figure S3.16. J - V characteristics of **s-CBZ:PC₇₁BM** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (56 ± 5 and 86 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

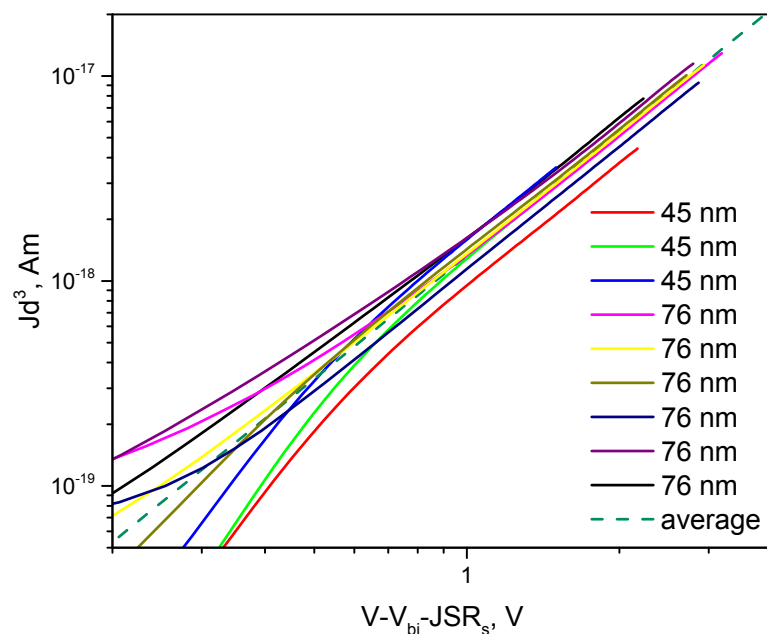


Figure S3.17. J - V characteristics of **t-CBZ:PC₇₁BM** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (45 ± 5 and 76 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

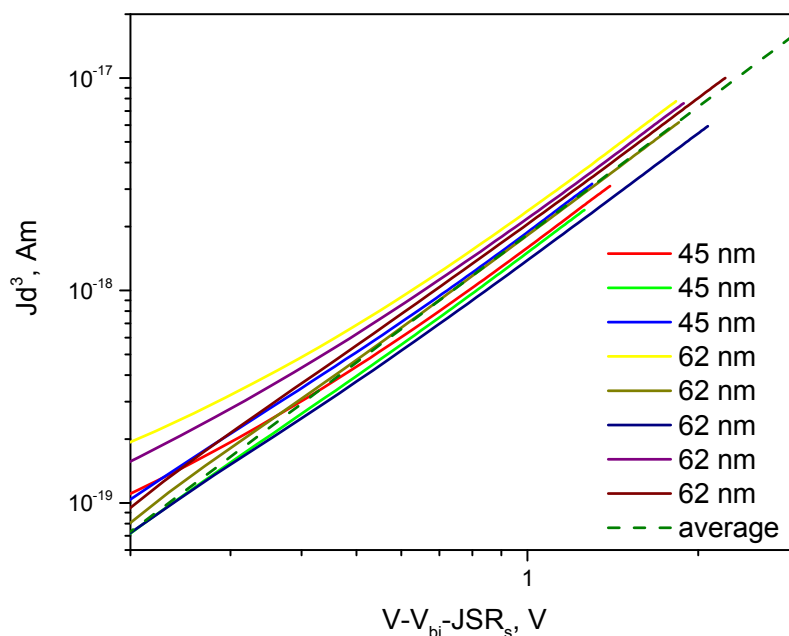


Figure S3.18. J - V characteristics of **BTI:PC₇₁BM** hole only devices (solid lines). Jd^3 is plotted for two different layer thicknesses (45 ± 5 and 62 ± 5 nm) against the voltage, corrected for the built-in voltage and the electrode series resistance. Dashed line represents SCLC-fit, from which the hole mobility is extracted.

3.6. Surface morphology of pristine films

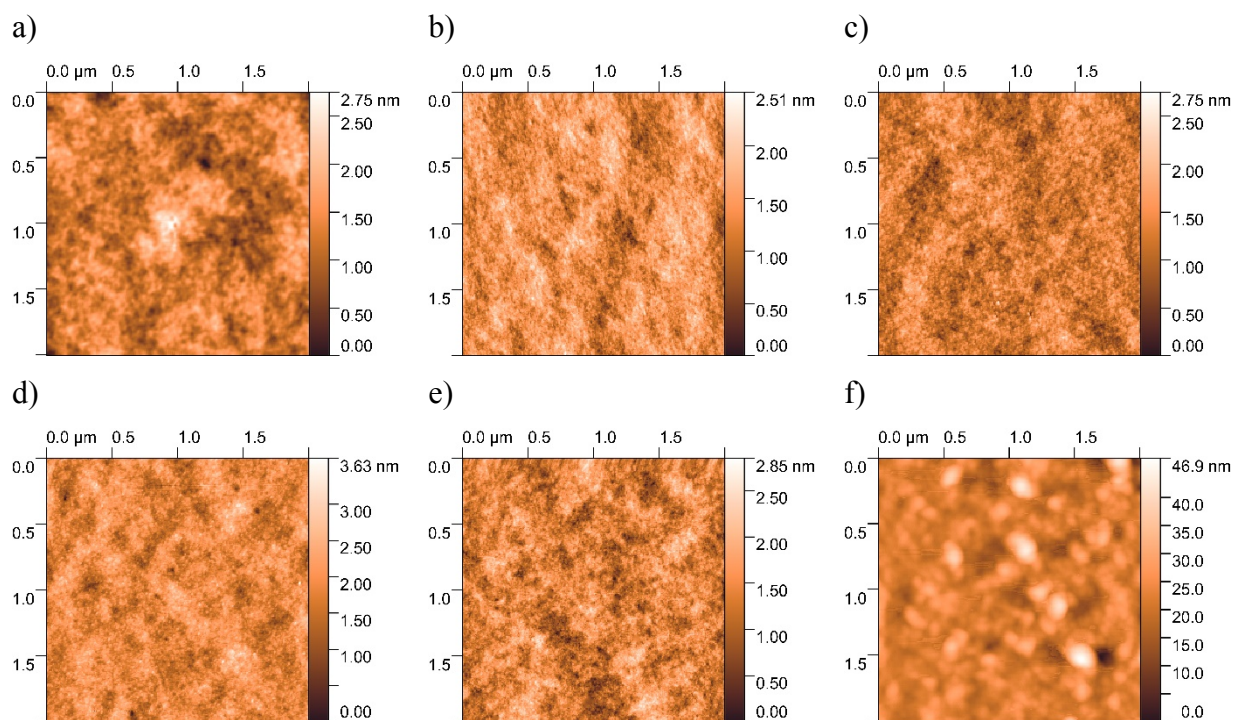


Figure S3.19. AFM surface scans of films of **TPA**, RMS=0.33 nm (a); **m-TPA**, RMS=0.31 nm (b); **f-TPA**, RMS=0.30 nm (c); **s-CBZ**, RMS=0.36 nm (d); **t-CBZ**, RMS=0.37 nm (e); **BTI**, RMS=4.60 nm (f).

3.7. Surface morphology of blended films

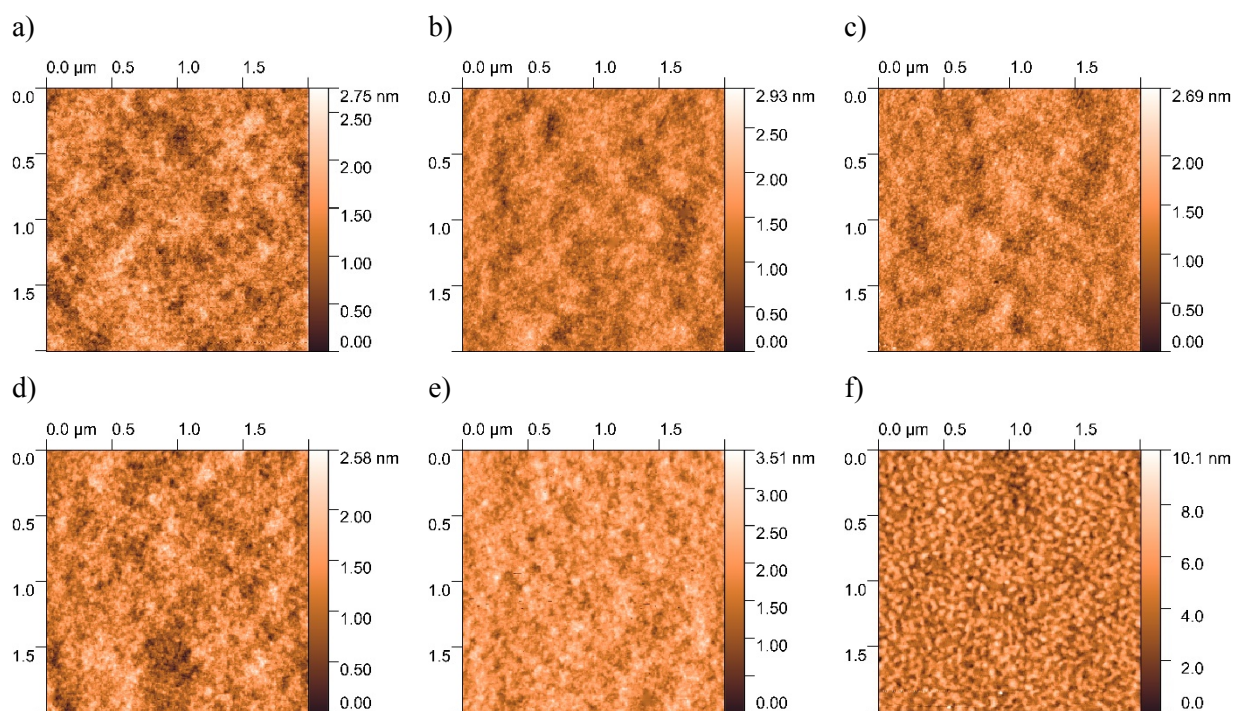


Figure S3.20. AFM surface scans of films of **TPA:PC₇₁BM**, RMS=0.36 nm (a); **m-TPA:PC₇₁BM**, RMS=0.30 nm (b); **f-TPA:PC₇₁BM**, RMS=0.31 nm (c); **s-CBZ:PC₇₁BM**, RMS=0.33 nm (d); **t-CBZ:PC₇₁BM**, RMS=0.36 nm (e); **BTI:PC₇₁BM**, RMS=1.28 nm (f).

3.7. Averaged photovoltaic parameters

Table S1. Photovoltaic parameters of SCOSCs under AM1.5G illumination (100 mW/cm²) averaged over eight devices.

Active layer material	J_{sc} , mA/cm ²	V_{oc} , V	FF, %	PCE, %
TPA	1.66 ± 0.05	1.06 ± 0.13	24.7 ± 1.1	0.43 ± 0.04
m-TPA	1.628 ± 0.018	0.96 ± 0.14	24.6 ± 1.0	0.38 ± 0.04
f-TPA	0.524 ± 0.008	0.57 ± 0.10	27.3 ± 1.1	0.081 ± 0.011
s-CBZ	1.32 ± 0.05	1.01 ± 0.08	24.7 ± 0.5	0.327 ± 0.013
t-CBZ	0.452 ± 0.018	0.92 ± 0.17	23.3 ± 1.8	0.096 ± 0.013
BTI	3.962 ± 0.028	0.755 ± 0.020	30.4 ± 0.5	0.910 ± 0.021

Table S2. Photovoltaic parameters of BHJ solar cells under AM1.5G illumination (100 mW/cm²) averaged over eight devices.

Active layer	J_{sc} , mA/cm ²	V_{oc} , V	FF, %	PCE, %
TPA:PC₇₁BM	7.91 ± 0.10	0.983 ± 0.009	45.0 ± 0.8	3.50 ± 0.12
m-TPA:PC₇₁BM	6.87 ± 0.23	0.8892 ± 0.0014	38.2 ± 0.8	2.34 ± 0.13
f-TPA:PC₇₁BM	8.64 ± 0.04	1.004 ± 0.010	38.5 ± 1.0	3.34 ± 0.12
s-CBZ:PC₇₁BM	4.95 ± 0.14	1.060 ± 0.012	30.81 ± 0.16	1.617 ± 0.029
t-CBZ:PC₇₁BM	2.01 ± 0.04	0.81 ± 0.12	28.2 ± 1.3	0.46 ± 0.07
BTI:PC₇₁BM	7.58 ± 0.10	0.936 ± 0.004	50.5 ± 1.9	3.59 ± 0.18

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